



Correction to: Investigation of MOCVD grown crack-free 4 μm thick aluminum nitride using nitrogen as a carrier gas

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The Authors would like to correct text in the introduction of the article.

The sentence: Nitrogen (N₂) has previously been used as a carrier gas to grow AlN, resulting in inferior material quality [11–13].

Should read: Kakanakova-Georgieva et al. first demonstrated that AlN growth on SiC substrate using nitrogen (N₂) as carrier gas can be beneficial, on the other hand, Miyagawa et al. reported that the use of N₂ carrier gas resulted in inferior material quality compared to H₂ carrier gas on sapphire substrate [11–13].”

The original article can be found online at <https://doi.org/10.1557/s43580-021-00071-8>.

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